

Electronic Supplementary Information

The correlations of the electronic structure and film growth of 2,7-diocty[1]benzothieno[3,2-b]benzothiophene (C8-BTBT) on SiO₂

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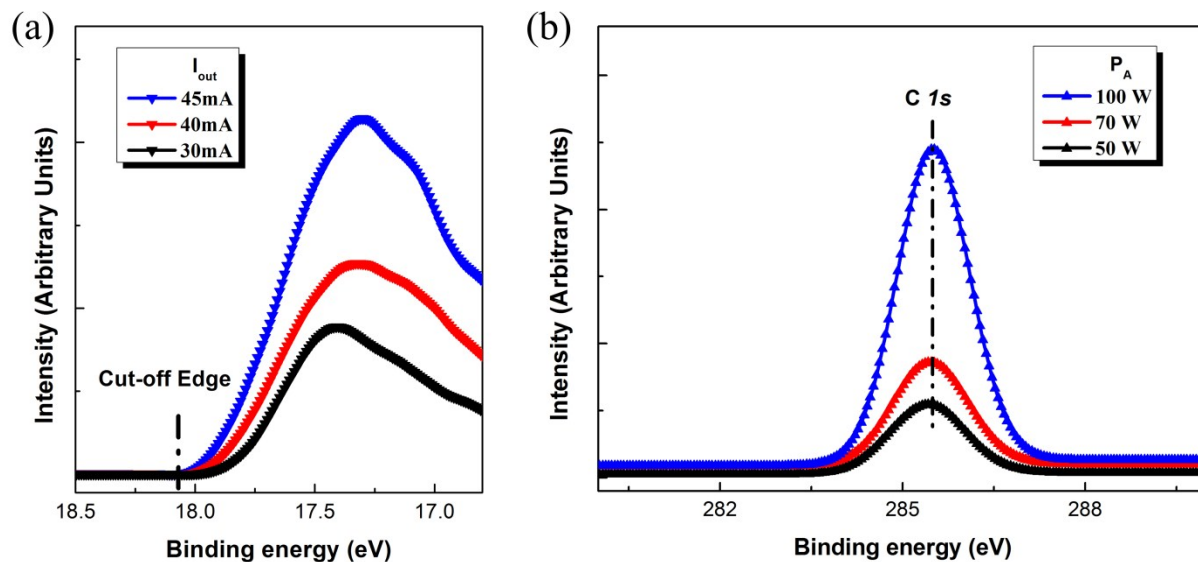


Fig. S1 (a) UPS cut-off region of 8.0 nm C8-BTBT on SiO₂ at different out current (I_{out}) of UV lamp and (b) XPS C 1s core-level at different anode power dissipation (P_A) of X-ray.

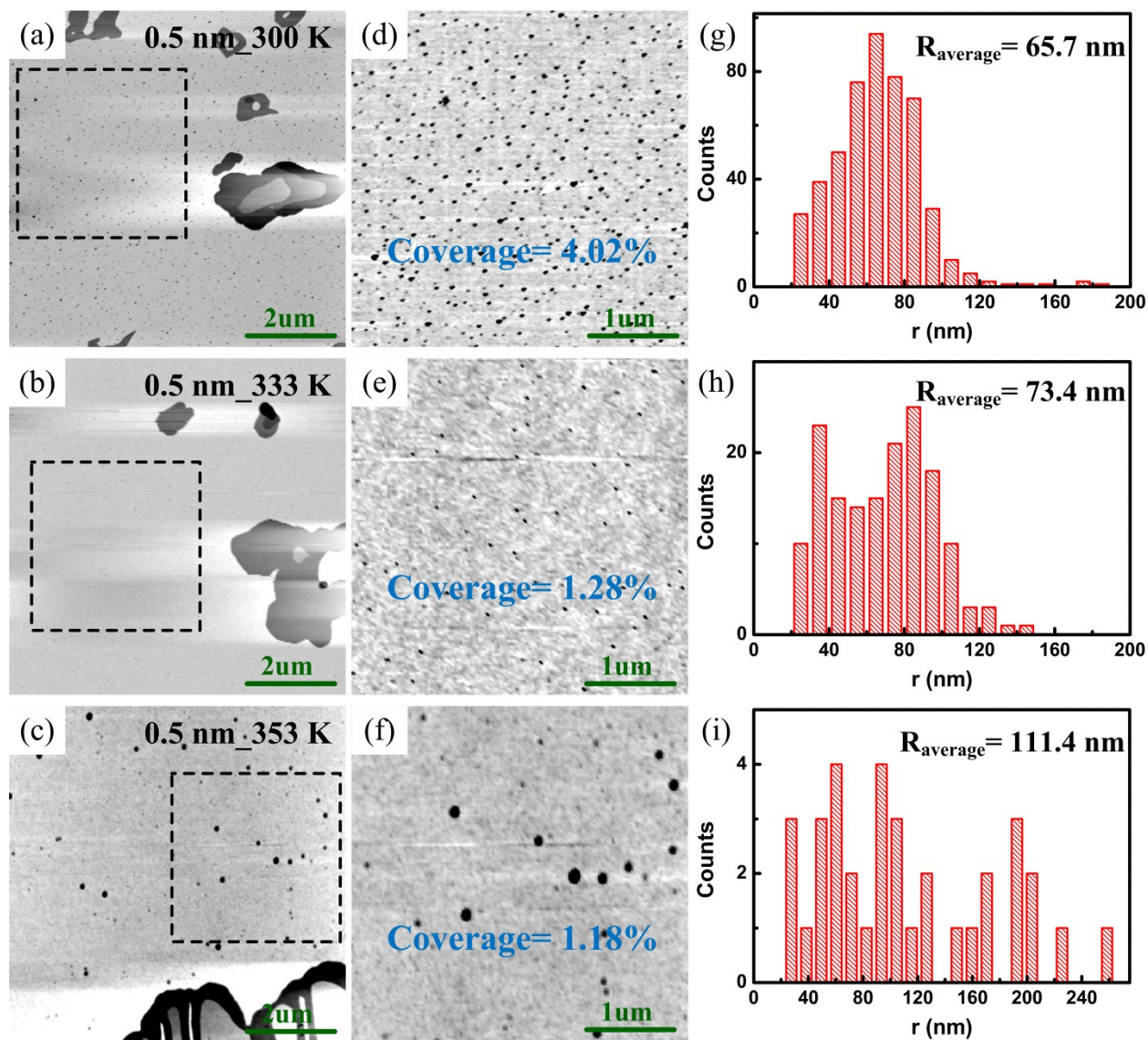


Fig. S2 AFM morphology images ($10 \mu\text{m} \times 10 \mu\text{m}$) of 0.5 nm-thick C8-BTBT films on SiO₂ as a function of substrate temperature of (a) 300, (b) 333, (c) 353 K. (d)-(f) are the corresponding magnified image ($5.0 \mu\text{m} \times 5.0 \mu\text{m}$) from the crystallites region indicated by black dashed square in (a)-(c). The histograms of (g), (h) and (i) show the radius distribution of crystallites in (d), (e) and (f), respectively.